

Dual enhanced ultrafast power diode

Rev. 02 - 7 November 2018

**Product data sheet** 

### 1. General description

Dual enhanced ultrafast power diode in a SOT186A (TO-220AB) plastic package.

### 2. Features and benefits

- High thermal cycling performance
- Isolated package
- Low thermal resistance
- Soft recovery characteristic minimizes power consuming oscillations
- Very low on-state losses

### 3. Applications

- Dual mode (DCM and CCM) PFC
- Power Factor Correction (PFC) for Interleaved Topology

### 4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Mir	т Тур	Max	Unit
V <sub>R</sub>	reverse voltage	DC	-	-	600	V
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; SIN; per diode	-	-	132	A
		t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 25 °C; SIN; per diode	-	-	120	A
Static chara	acteristics		· ·			
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 4</u>	-	1.4	2.1	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C	-	1.3	1.9	V
Dynamic ch	naracteristics					
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s}; \\ T_j = 25 \text{ °C}; \text{ Fig. 5}$	-	20	35	ns

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# 5. Pinning information

Table 2. F	Pinning in	formation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	mb	
2	К	cathode		
3	A2	anode 2		K sym125
mb	n.c.	mounting base; isolated	() () () () () () () () () () () () () (	

# 6. Ordering information

Table 3. Ordering information						
Type number	Package	ge				
	Name	Description	Version			
BYV410X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A			

BYV410X-600

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### 7. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage		-	600	V
V <sub>RWM</sub>	crest working reverse voltage		-	600	V
V <sub>R</sub>	reverse voltage	DC	-	600	V
I <sub>O(AV)</sub>	average output current	$\delta$ = 0.5 ; T <sub>h</sub> ≤ 42 °C; SQW; both diodes conducting; Fig. 1; Fig. 2	-	20	A
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 $\ ; t_p$ = 25 µs; $T_h \leq \ 60 \ ^\circ C;$ SQW; per diode	-	20	A
I <sub>FSM</sub>	non-repetitive peak	$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; SIN; per diode	-	132	А
	forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; SIN; per diode	-	120	А
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

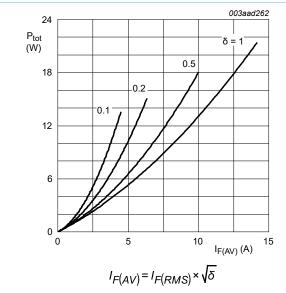


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

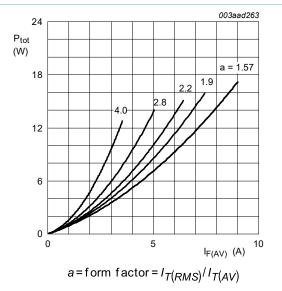


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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### 8. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-h)</sub>	thermal resistance from junction to	with heatsink compound; per diode; Fig. 3	-	-	5	K/W
	heatsink	with heatsink compound; both diodes conducting	-	-	3.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air		-	55	-	K/W

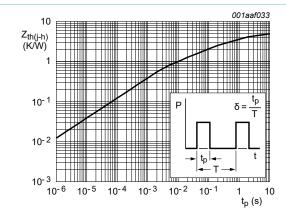


Fig. 3. Transient thermal impedance from junction to heatsink per diode as a function of pulse width

# 9. Isolation characteristics

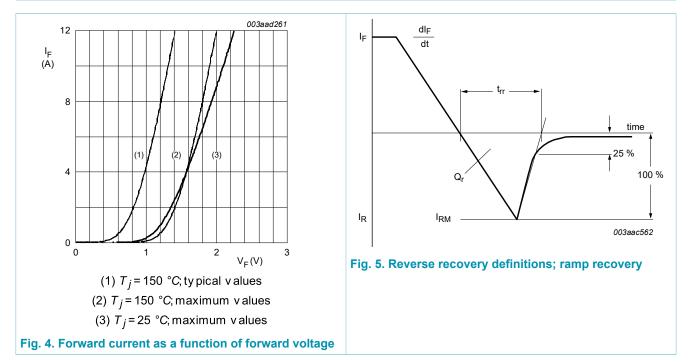
Table 6. Isolation characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	50 Hz < f < 60 Hz; sinusoidal waveform; relative humidity < 65 %; clean and dust free; from all terminals to external heatsink		-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from cathode to external heatsink; f = 1 MHz		-	10	-	pF

Table 5 Thermal characteristics

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### **10. Characteristics**

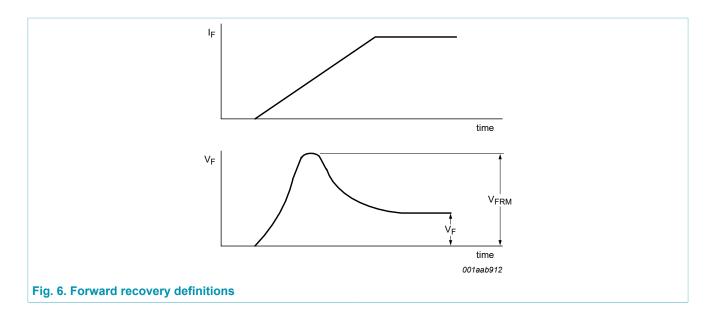
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · · · ·				
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 4</u>	-	1.4	2.1	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C	-	1.3	1.9	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 100 °C	-	1	1.5	mA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	13	50	μA
Dynamic ch	naracteristics					
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 5}$	-	20	35	ns
I <sub>RM</sub>	peak reverse recovery current	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 100 A/μs; <u>Fig. 5</u>	-	1.4	1.9	A
Q <sub>r</sub>	recovered charge	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 100 A/μs	-	15	28	nC
V <sub>FR</sub>	forward recovery voltage	I <sub>F</sub> = 1 A; dI <sub>F</sub> /dt = 100 A/μs; <u>Fig. 6</u>	-	3.2	-	V



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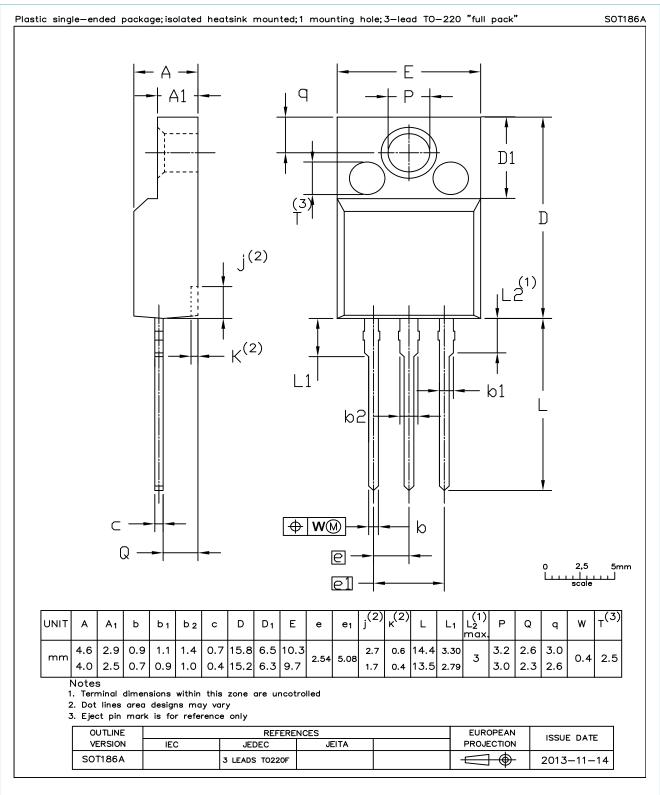
# BYV410X-600

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### 11. Package outline



### Fig. 7. Package outline TO-220F (SOT186A)

BYV410X-600

# **12. Revision history**

Table 8. Revision history							
Document ID	Release date	Data sheet status	Change notice	Supersedes			
BYV410X-600 v.2	20181107	Product data sheet	-	BYV410X-600 v.1			
Modifications: Change from NXP version to WeEn version and update Rth.							
BYV410X-600 v.1	20180920	Product data sheet	-	-			

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### 13. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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